Schottky barrier diode

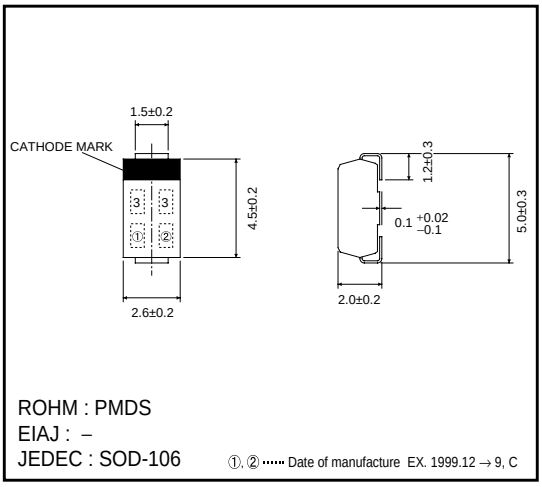
RB161L-40

●**Applications**
High frequency rectification
For switching power supply

●**Features**
1) Compact power mold type. (PMDS)
2) Ultra low V_F.(V_F=0.35V Typ. at 1A)
3) V_{RM}=40V guaranteed.

●**Construction**
Silicon epitaxial planar

●**External dimensions** (Units : mm)



ROHM : PMDS
EIAJ : –
JEDEC : SOD-106
①, ② ····· Date of manufacture EX. 1999.12 → 9, C

●**Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	20	V
Mean rectifying current ∗	I_O	1	A
Peak forward surge current	I_{FSM}	70	A
Junction temperature	Tj	125	˚C
Storage temperature	Tstg	–40~+125	˚C

∗ When mounting on PCB

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	–	0.40	V	I_F=1.0A
Reverse current	I_R	–	–	1	mA	V_R=20V

●**Electrical characteristic curves** (Ta=25°C)

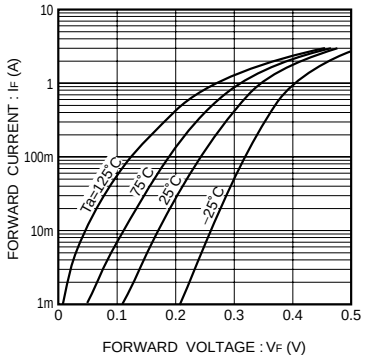


Fig.1 Forward characteristics

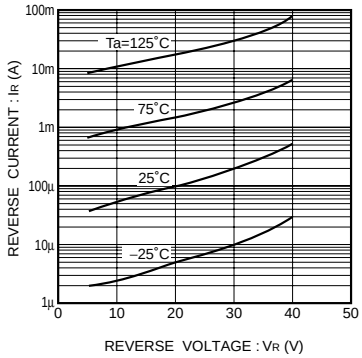


Fig.2 Reverse characteristics

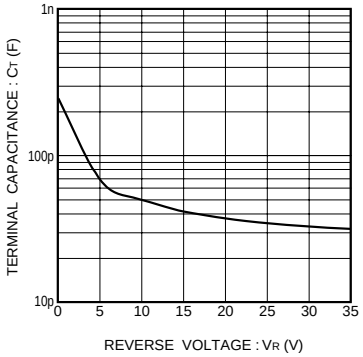


Fig.3 Capacitance between terminals characteristics

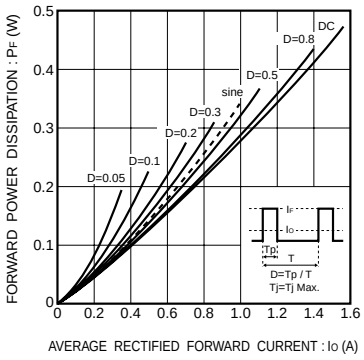


Fig.4 Forward power dissipation characteristics

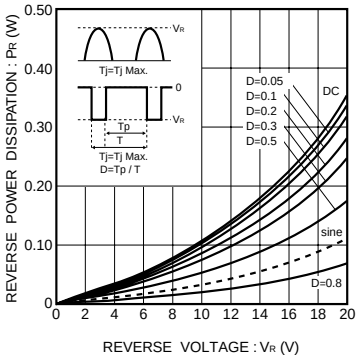


Fig.5 Reverse power dissipation characteristics

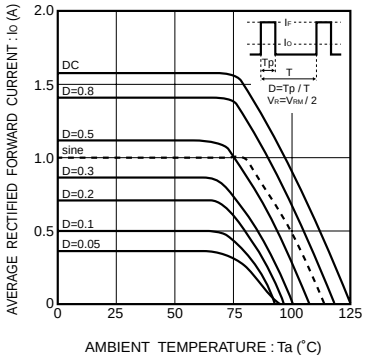


Fig.6 Derating curve (when mounting on glass epoxy PCBs)